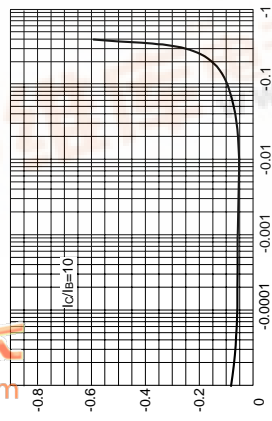


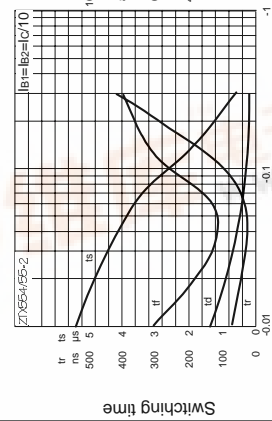
# ZTX554 ZTX555

## TYPICAL CHARACTERISTICS



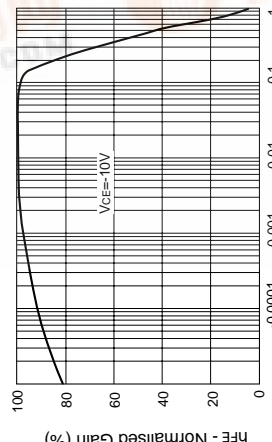
IC - Collector Current (Amps)

VCE(sat) v IC



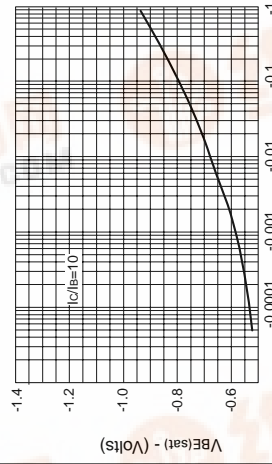
IC - Collector Current (Amps)

Switching Speeds



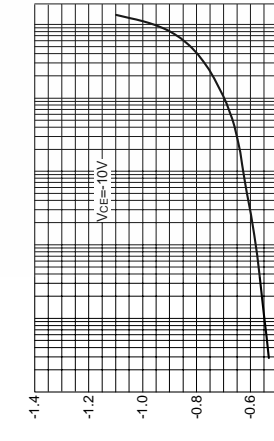
IC - Collector Current (Amps)

hFE v IC



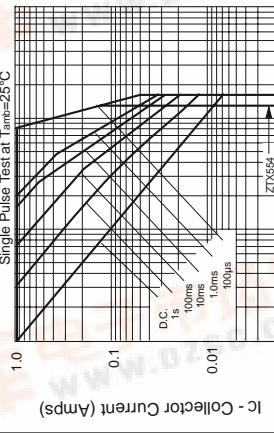
IC - Collector Current (Amps)

VBE(sat) v IC



IC - Collector Current (Amps)

VBE(on) v IC



IC - Collector Current (Amps)

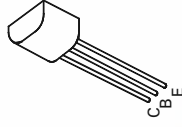
Safe Operating Area

# PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

ISSUE 1 - MARCH 94

## FEATURES

- \* 150 Volt V<sub>CEO</sub>
- \* 1 Amp continuous current
- \* P<sub>tot</sub> = 1 Watt



E-Line

TO92 Compatible

## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	ZTX554	ZTX555	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	-140	-160	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-125	-150	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	-5	V
Peak Pulse Current	I <sub>CM</sub>	-2	-2	A
Continuous Collector Current	I <sub>C</sub>	-1	-1	A
Power Dissipation: at T <sub>amb</sub> = 25°C derate above 25°C	P <sub>tot</sub>	1	5.7	W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55 to +200		°C

## ELECTRICAL CHARACTERISTICS (at T<sub>amb</sub> = 25°C unless otherwise stated).

PARAMETER	SYMBOL	ZTX554		ZTX555		UNIT	CONDITIONS.
		MIN.	MAX	MIN.	MAX		
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-140		-160		V	I <sub>C</sub> = -100µA
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-125		-150		V	I <sub>C</sub> = -10mA*
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-5		-5		V	I <sub>E</sub> = -100µA
Collector Cut-Off Current	I <sub>CBO</sub>	-0.1		-0.1		µA	V <sub>CB</sub> = -120V V <sub>CE</sub> = -140V
Emitter Cut-Off Current	I <sub>EBO</sub>	-0.1		-0.1		µA	V <sub>EB</sub> = -4V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	-0.3		-0.3		V	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA*
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	-1		-1		V	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA*
Base-Emitter Turn-on Voltage	V <sub>BE(on)</sub>	-1		-1		V	I <sub>C</sub> = -100mA, V <sub>CE</sub> = -10V*
Static Forward Current Transfer Ratio	h <sub>FE</sub>	50	300	50	300		I <sub>C</sub> = -10mA, V <sub>CE</sub> = -10V* I <sub>C</sub> = -300mA, V <sub>CE</sub> = -10V*
Transition Frequency	f <sub>T</sub>	100		100		MHz	I <sub>C</sub> = -50mA, V <sub>CE</sub> = -10V f = 100MHz
Output Capacitance	C <sub>ob0</sub>	10		10		pF	V <sub>CE</sub> = -10V, f = 1MHz

查询ZTX554供应商

捷多邦, 专业PCB打样工厂, 24小时加急出货

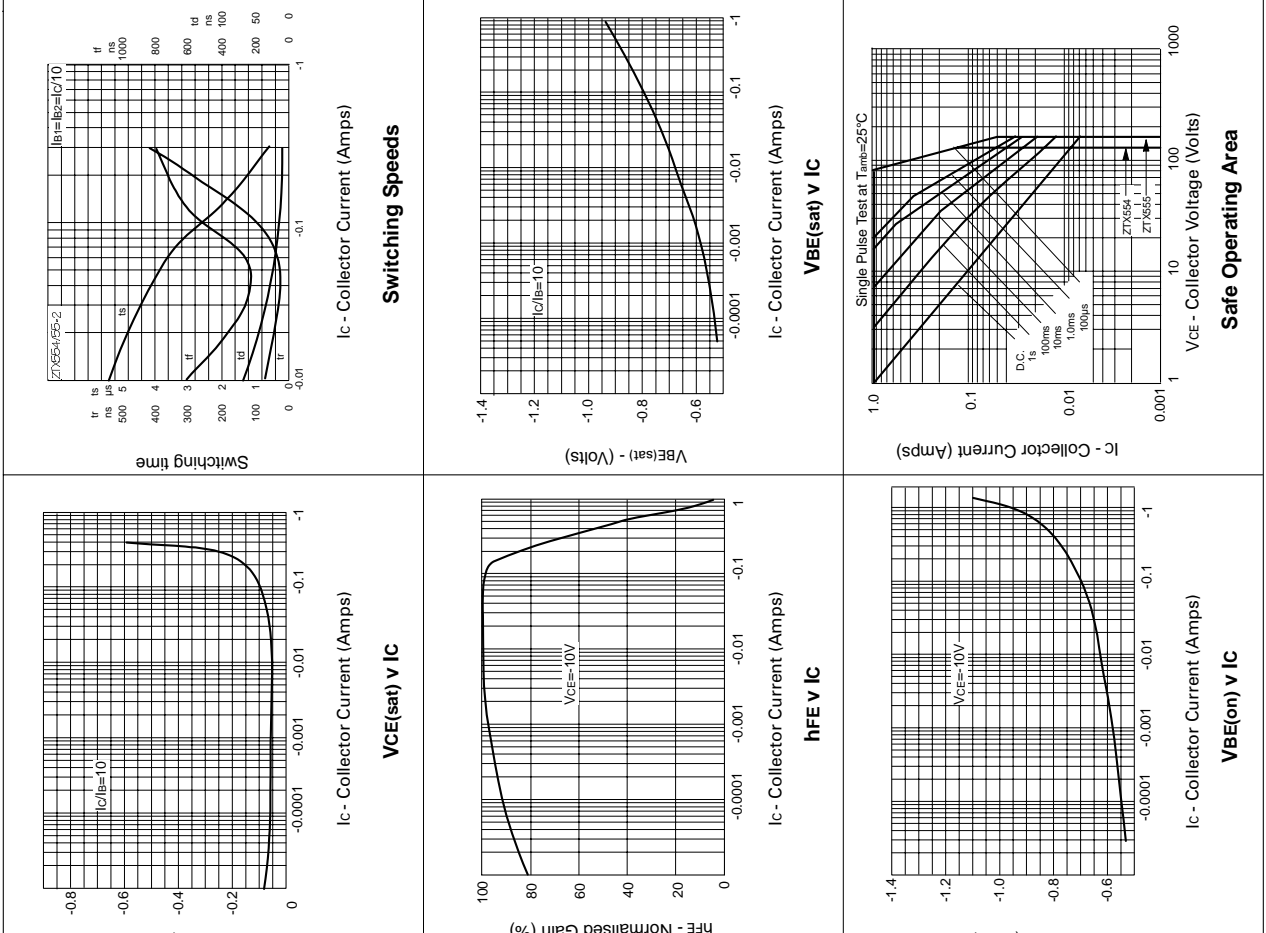
# ZTX554 ZTX555

# PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

# ZTX554 ZTX555

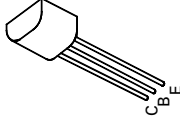
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## TYPICAL CHARACTERISTICS



## FEATURES

- \* 150 Volt  $V_{CE0}$
- \* 1 Amp continuous current
- \*  $P_{tot} = 1$  Watt



E-Line  
TO92 Compatible

## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	ZTX554	ZTX555	UNIT
Collector-Base Voltage	$V_{CBO}$	-140	-160	V
Collector-Emitter Voltage	$V_{CEO}$	-125	-150	V
Emitter-Base Voltage	$V_{EBO}$	-5	-5	V
Peak Pulse Current	$I_{CM}$	-2	-2	A
Continuous Collector Current	$I_C$	-1	-1	A
Power Dissipation: at $T_{amb} = 25^\circ C$ derate above $25^\circ C$	$P_{tot}$	1	5.7	W
Operating and Storage Temperature Range	$T_{j, stg}$	-55 to +200		$^\circ C$

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$ unless otherwise stated).

PARAMETER	SYMBOL	ZTX554		ZTX555		UNIT	CONDITIONS.
		MIN.	MAX	MIN.	MAX		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-140		-160		V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-125		-150		V	$I_C = -10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		-5		V	$I_E = -100\mu A$
Collector Cut-Off Current	$I_{CBO}$	-0.1		-0.1		$\mu A$	$V_{CB} = -120V$ $V_{CE} = -140V$
Emitter Cut-Off Current	$I_{EBO}$	-0.1		-0.1		$\mu A$	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-0.3		-0.3		V	$I_C = -100mA, I_B = -10mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-1		-1		V	$I_C = -100mA, I_B = -10mA^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$	-1		-1		V	$I_C = -100mA, V_{CE} = -10V^*$
Static Forward Current Transfer Ratio	$h_{FE}$	50	300	50	300		$I_C = -10mA, V_{CE} = -10V^*$ $I_C = -300mA, V_{CE} = -10V^*$
Transition Frequency	$f_T$	100		100		MHz	$I_C = -50mA, V_{CE} = -10V$ $f = 100MHz$
Output Capacitance	$C_{ob0}$	10		10		pF	$V_{CB} = -10V, f = 1MHz$